Hangyang Chen

List of Publications by Year
in descending order

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		1684188	1281871
11	129	5	11
papers	citations	h-index	g-index

11	11	11	195
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Regulating the Valence Level Arrangement of High-Al-content AlGaN Quantum Wells Using Additional Potentials with Mg Doping. Physical Chemistry Chemical Physics, 2022, , .	2.8	1
2	Integral Monolayer-Scale Featured Digital-Alloyed AlN/GaN Superlattices Using Hierarchical Growth Units. Crystal Growth and Design, 2019, 19, 1720-1727.	3.0	19
3	Modification of strain and optical polarization property in AlGaN multiple quantum wells by introducing ultrathin AlN layer. AIP Advances, 2019, 9, .	1.3	2
4	Improved Characteristics of AlGaN-Based Deep Ultraviolet Light-Emitting Diodes with Superlattice p-Type Doping. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	21
5	High density GaN/AlN quantum dots for deep UV LED with high quantum efficiency and temperature stability. Scientific Reports, 2014, 4, 5166.	3.3	38
6	Vacuum Rabi Splitting of Excitonâ€“Polariton Emission in an AlN Film. Scientific Reports, 2013, 3, 3551.	3.3	10
7	Symmetrically abrupt GaN/AlGaN superlattices by alternative interfaceâ€“interruption scheme. Journal of Materials Research, 2013, 28, 716-722.	2.6	6
8	Control of two-dimensional growth of AlN and high Al-content AlGaN-based MQWs for deep-UV LEDs. AIP Advances, 2013, 3, 052103.	1.3	5
9	Structural properties of InN films grown in different conditions by metalorganic vapor phase epitaxy. Journal of Materials Research, 2011, 26, 775-780.	2.6	4
10	Origins and suppressions of parasitic emissions in ultraviolet light-emitting diode structures. Journal of Materials Research, 2010, 25, 1037-1040.	2.6	4
11	Enhancement of p-type conductivity by modifying the internal electric field in Mg- and Si-Î´-codoped AlxGa1â^'xN/AlyGa1â^'yN superlattices. Applied Physics Letters, 2009, 95, .	3.3	19